## NSN 5961-01-045-8242

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View Online at https://aerobasegroup.com/nsn/5961-01-045-8242	
Inclosure Material:	
Metal	
Overall Length:	
Between 0.428 inches and 0.535 inches	
Mounting Facility Quantity:	
1	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed case	
Overall Width Across Flats:	
Between 0.551 inches and 0.559 inches	
Thread Size:	
0.250 inches	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
50.0 repetitive peak reverse voltage and 75.0 nonrepetitive peak reverse voltage and 50.0 repetitive peak off-state voltage	
Current Rating Per Characteristic:	
20.00 amperes forward current, total rms horsepower metric and 240.00 amperes forward current, total rms watts	
Power Rating Per Characteristic:	
5.0 watts small-signal input power, common-collector blank	
Maximum Operating Tempurature Per Measurement Point:	
100.0 degrees celsius junction	
Test Data Document:	
09448-hy233-5 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, e	tc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)	
Thread Series Designator:	
Unf	
Terminal Type And Quantity:	
1 threaded stud and 2 tab, solder lug	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	